

ABSTRACT OF THE DISCLOSURE

An integrated power device having a power transistor made up of a first diode and a second diode that are connected together in series between a collector region and emitter-contact region of the power transistor to define a common intermediate node, a control circuit including a high-voltage region bonded on the emitter-contact region (14) by means of an adhesive layer, and biasing circuit connected between the common intermediate node and the high-voltage region. The biasing circuit including a contact pad electrically connected to the common intermediate node, an electrical connection region that is in electrical contact with the high-voltage region (30), and a wire having a first end soldered on the contact pad and a second end soldered on said electrical connection region.

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